

Triacs

Silicon Bidirectional Triode Thyristors

... designed primarily for industrial and military applications for the control of ac loads in applications such as light dimmers, power supplies, heating controls, motor controls, welding equipment and power switching systems; or wherever full-wave, silicon gate controlled solid-state devices are needed.

- Glass Passivated Junctions and Center Gate Fire
- Isolated Stud for Ease of Assembly
- Gate Triggering Guaranteed In All 4 Quadrants

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
*Peak Repetitive Off-State Voltage ($T_J = -65$ to $+125^\circ\text{C}$) 1/2 Sine Wave 50 to 60 Hz, Gate Open	V_{DRM}		Volts
*Peak Principal Voltage			
2N6157, 2N6160, 2N6163		200	
2N6158, 2N6161, 2N6164		400	
2N6159, 2N6162, 2N6165		600	
*Peak Gate Voltage	V_{GM}	10	Volts
*RMS On-State Current ($T_C = -65$ to $+85^\circ\text{C}$) ($T_C = +100^\circ\text{C}$) Full Sine Wave, 50 to 60 Hz	$I_T(\text{RMS})$	30 20	Amps
*Peak Non-Repetitive Surge Current (One Full Cycle of surge current at 60 Hz, preceded and followed by a 30 A RMS current, $T_C = 85^\circ\text{C}$)	I_{TSM}	250	Amps
Circuit Fusing Considerations ($t = 8.3$ ms)	I^2t	260	A^2s
*Peak Gate Power ($T_J = +80^\circ\text{C}$, Pulse Width = $2 \mu\text{s}$)	P_{GM}	20	Watts
*Average Gate Power ($T_J = +80^\circ\text{C}$, $t = 8.3$ ms)	$P_{G(AV)}$	0.5	Watt
*Peak Gate Current	I_{GM}	2	Amps
*Operating Junction Temperature Range	T_J	-65 to $+125$	$^\circ\text{C}$
*Storage Temperature Range	T_{stg}	-65 to $+150$	$^\circ\text{C}$
*Stud Torque 2N6160 thru 2N6165	—	30	in. lb.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
*Thermal Resistance, Junction to Case	$R_{\theta JC}$	1	$^\circ\text{C}/\text{W}$

*Indicates JEDEC Registered Data

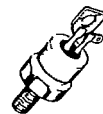
2N6145-47
(See 2N5571)

2N6157
thru
2N6165

TRIACS
30 AMPERES RMS
200 thru 600 VOLTS



CASE 174-04
(TO-203AA)
STYLE 3
2N6157-59



CASE 263-04
STYLE 2
2N6160-62



CASE 311-02
STYLE 2
2N6163-65

Characteristic	Symbol	Min	Typ	Max	Unit
*Peak Forward or Reverse Blocking Current (Rated V _{DRM} or V _{RRM}) T _J = 25°C T _J = 125°C	I _{DRM} , I _{RRM}	—	—	10 2	μA mA
*Peak On-State Voltage (Either Direction) (I _{TM} = 42 A Peak, Pulse Width = 1 to 2 ms, Duty Cycle ≤ 2%)	V _{TM}	—	1.5	2	Volts
Gate Trigger Current (Continuous dc), Note 1 (Main Terminal Voltage = 12 Vdc, R _L = 50 Ohms)	I _{GT}	—	15	60	mA
MT2(+), G(+)	—	—	20	70	
MT2(+), G(-)	—	—	20	70	
MT2(-), G(-)	—	—	30	100	
MT2(-), G(+)	—	—	—	200	
*MT2(+), G(+); MT2(-), G(-) T _C = -65°C	—	—	—	250	
*MT2(+), G(-); MT2(-), G(+)	—	—	—	—	
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, R _L = 50 Ohms)	V _{GT}	—	0.8	2	Volts
MT2(+), G(+)	—	—	0.7	2.1	
MT2(+), G(-)	—	—	0.85	2.1	
MT2(-), G(-)	—	—	1.1	2.5	
MT2(-), G(+)	—	—	—	3.4	
*All Quadrants, T _C = -65°C	—	—	—	—	
*Main Terminal Voltage = Rated V _{DRM} , R _L = 10 k ohms, T _J = +125°C	—	0.2	—	—	
Holding Current (Main Terminal Voltage = 12 Vdc, Gate Open) (Initiating Current = 500 mA)	I _H	—	8	70	mA
MT2(+)	—	—	10	80	
MT2(-)	—	—	—	200	
*Either Direction, T _C = -65°C	—	—	—	—	
*Turn-On Time (Main Terminal Voltage = Rated V _{DRM} , I _{TM} = 42 A, Gate Source Voltage = 12 V, R _S = 50 Ohms, Rise Time = 0.1 μs, Pulse Width = 2 μs)	t _{gt}	—	1	2	μs
Blocking Voltage Application Rate at Commutation, f = 60 Hz, T _C = 85°C On-State Conditions: (I _{TM} = 42 A, Pulse Width = 4 ms, di/dt = 17.5 A/ms) Off-State Conditions: (Main Terminal Voltage = Rated V _{DRM} (200 μs min), Gate Source Voltage = 0 V, R _S = 50 Ω)	dv/dt(c)	—	5	—	V/μs

*Indicates JEDEC Registered Data.

Note 1. All voltage polarities referenced to main terminal 1.

FIGURE 1 - RMS CURRENT DERATING

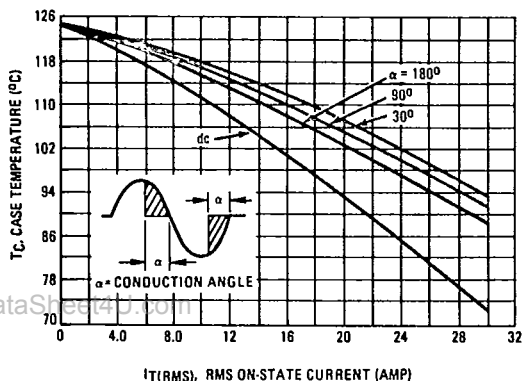


FIGURE 2 - POWER DISSIPATION

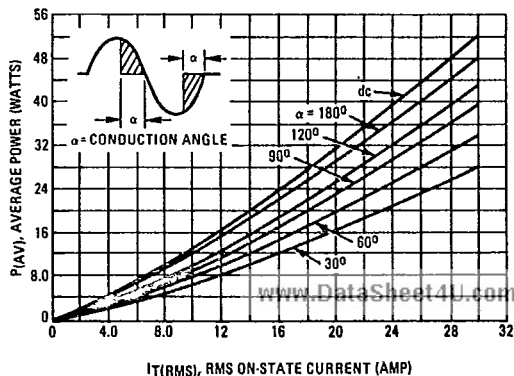


FIGURE 3 – TYPICAL GATE TRIGGER VOLTAGE

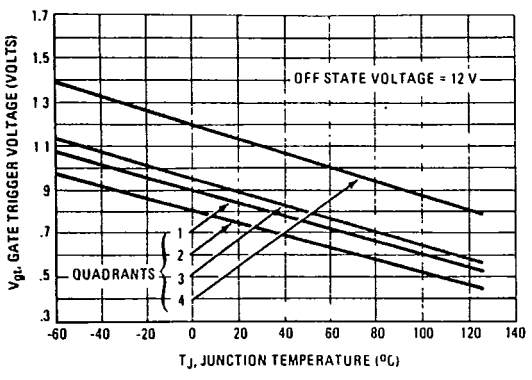


FIGURE 4 – TYPICAL GATE TRIGGER CURRENT

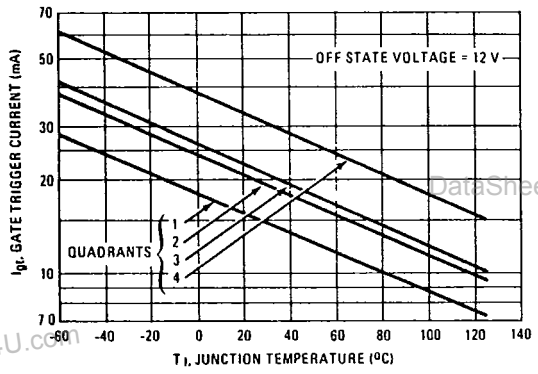


FIGURE 6 – TYPICAL HOLDING CURRENT

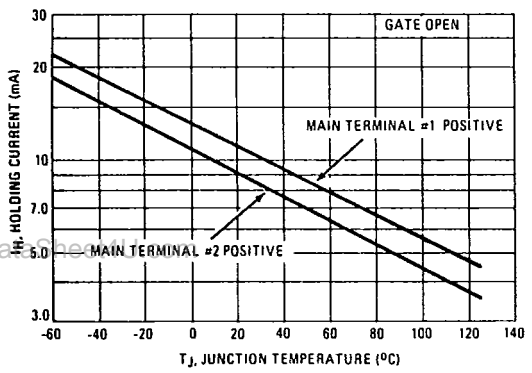


FIGURE 5 – MAXIMUM ON-STATE CHARACTERISTICS

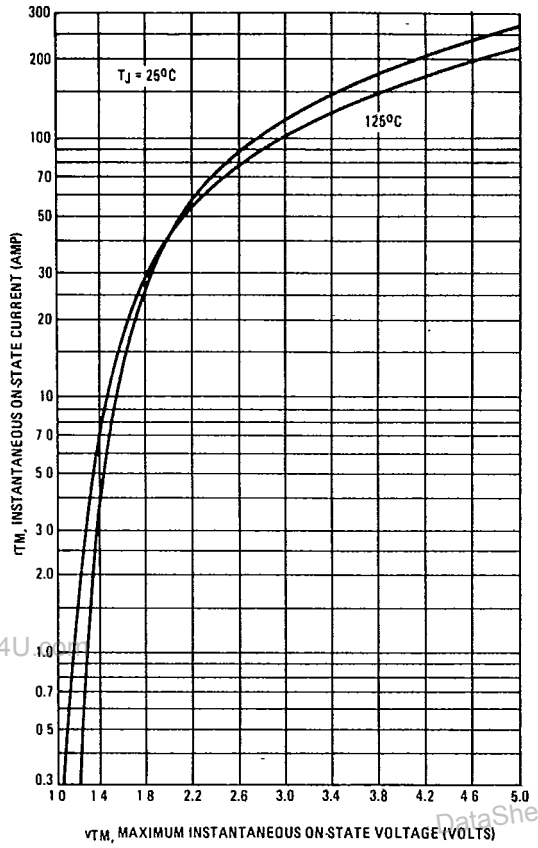


FIGURE 7 – MAXIMUM ALLOWABLE SURGE CURRENT

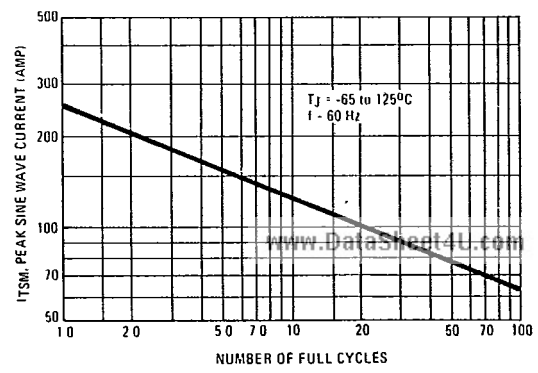


FIGURE 8 - TYPICAL THERMAL RESPONSE

1-23

